

isc N-Channel MOSFET Transistor

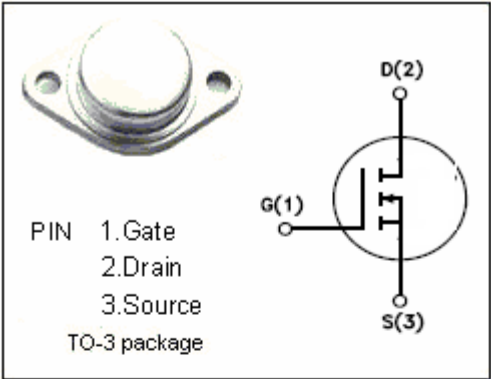
2N6766

DESCRIPTION

- VGS Rated at ±20V
- Silicon Gate for fast switching speeds
- IDSS 、 RDS(ON) . specified at elevated temperature
- Low drive requirements

APPLICATIONS

designed for high power ,high speed application ,such as switching applies,UPS,AC and DC motor controls , relay and high energy pulse circuits.

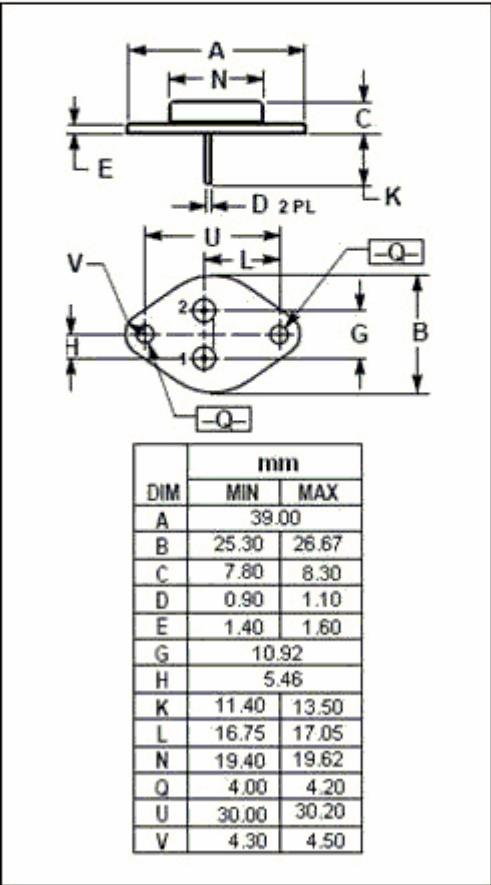


ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | ARAMETER                                  | VALUE   | UNIT |
|------------------|-------------------------------------------|---------|------|
| V <sub>DSS</sub> | Drain-Source Voltage (V <sub>GS</sub> =0) | 200     | V    |
| V <sub>GS</sub>  | Gate-Source Voltage                       | ±20     | V    |
| I <sub>D</sub>   | Drain Current-continuous@ TC=37℃          | 30      | A    |
| P <sub>tot</sub> | Total Dissipation@TC=25℃                  | 150     | W    |
| T <sub>j</sub>   | Max. Operating Junction Temperature       | -55~150 | ℃    |
| T <sub>stg</sub> | Storage Temperature Range                 | -55~150 | ℃    |

THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                           | MAX  | UNIT |
|---------------------|-------------------------------------|------|------|
| R <sub>th j-c</sub> | Thermal Resistance,Junction to Case | 0.83 | ℃/W  |



**isc N-Channel Mosfet Transistor****2N6766****• ELECTRICAL CHARACTERISTICS ( $T_C=25^{\circ}\text{C}$ )**

| SYMBOL        | PARAMETER                        | CONDITIONS                             | MIN | MAX   | UNIT     |
|---------------|----------------------------------|----------------------------------------|-----|-------|----------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage   | $V_{GS}=0$ ; $I_D=1\text{mA}$          | 200 |       | V        |
| $V_{GS(TH)}$  | Gate Threshold Voltage           | $V_{DS}=V_{GS}$ ; $I_D=1\text{mA}$     | 2   | 4     | V        |
| $R_{DS(ON)}$  | Drain-Source On-stage Resistance | $V_{GS}=10\text{V}$ ; $I_D=19\text{A}$ |     | 0.085 | $\Omega$ |
| $I_{GSS}$     | Gate Source Leakage Current      | $V_{GS}=20\text{V}$ ; $V_{DS}=0$       |     | 100   | nA       |
| $I_{DSS}$     | Zero Gate Voltage Drain Current  | $V_{DS}=200\text{V}$ ; $V_{GS}=0$      |     | 1     | mA       |
| $V_{SD}$      | Diode Forward Voltage            | $I_F=30\text{A}$ ; $V_{GS}=0$          |     | 1.8   | V        |